Abstracts

Development of a Pulsed IMPATT Diode Amplifier

B.E. Sigmon and T.W. Van Alstyne. "Development of a Pulsed IMPATT Diode Amplifier." 1986 MTT-S International Microwave Symposium Digest 86.1 (1986 [MWSYM]): 105-108.

The impedance transformation properties of parallel coupled lines have been used to develop broadband reflection amplifiers operating in X-band. These amplifiers have demonstrated peak powers of 40 watts (single IMPATT diode), 63 watts (two diode combiner), and 110 watts (four diode combiner). 3 dB bandwidths of 1.4 to 3 GHz (14 to 30%) have been attained.

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